

FEATURE

- Low gate charge
- Low C_{iss}
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

Maximum output current

 I_{OM} : 0.5 A

Output voltage

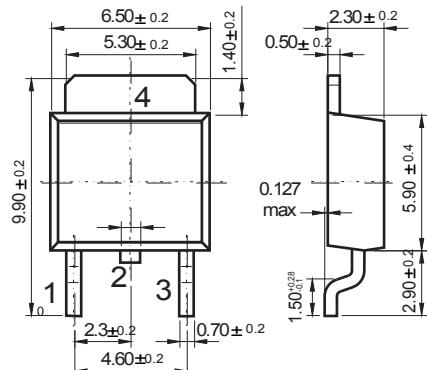
 V_O : 8V

Continuous total dissipation

 P_D : 1.25 W ($T_a = 25^\circ C$)

TO-252

Unit: mm



Dimensions in inches and (millimeters)

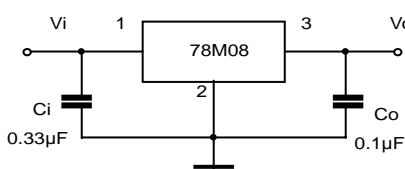
ABSOLUTE MAXIMUM RATINGS (Operating temperature range applies unless otherwise specified)

Parameter	Symbol	Value	Unit
Input Voltage	V_i	35	V
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	80	°C/W
Operating Junction Temperature Range	T_{OPR}	-40~+125	°C
Storage Temperature Range	T_{STG}	-65~+150	°C

 ELECTRICAL CHARACTERISTICS AT SPECIFIED VIRTUAL JUNCTION TEMPERATURE ($V_i=14V, I_o=350mA, C_i=0.33\mu F, C_o=0.1\mu F$, unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Output Voltage	V_o	$T_J=25^\circ C$	7.76	8	8.24	V
		$10.5 \leq V_i \leq 23V, I_o=5mA-350mA$	7.6	8	8.4	V
Load Regulation	ΔV_o	$I_o=5mA-500mA, T_J=25^\circ C$		20	160	mV
		$I_o=5mA-200mA, T_J=25^\circ C$		10	80	mV
Line Regulation	ΔV_o	$10.5V \leq V_i \leq 25V, I_o=200mA, T_J=25^\circ C$		6	100	mV
		$11V \leq V_i \leq 25V, I_o=200mA, T_J=25^\circ C$		2	50	mV
Quiescent Current	I_q	$T_J=25^\circ C$		4.6	6	mA
Quiescent Current Change	ΔI_q	$10.5V \leq V_i \leq 25V, I_o=200mA$			0.8	mA
	ΔI_q	$5mA \leq I_o \leq 350mA$			0.5	mA
Output Noise Voltage	V_N	$10Hz \leq f \leq 100KHz, T_J=25^\circ C$		52		µV/Vo
Ripple Rejection	RR	$11.5V \leq V_i \leq 21.5V, f=120Hz, I_o=300mA$	56	80		dB
Dropout Voltage	V_d	$I_o=350mA, T_J=25^\circ C$		2		V
Short Circuit Current	I_{sc}	$V_i=14V, T_J=25^\circ C$		250		mA
Peak Current	I_{pk}	$T_J=25^\circ C$		0.5		A

* Pulse test.

TYPICAL APPLICATION


Note: Bypass capacitors are recommended for optimum stability and transient response and should be located as close as possible to the regulators.

RATING AND CHARACTERISTIC CURVES (78M08)

